

## KSB1116/1116A

# **Audio Frequency Power Amplifier & Medium Speed Switching**

Complement to KSD1616/1616A



# **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Paramet	Parameter		Units
V <sub>CBO</sub>	Collector-Base Voltage	: KSB1116	-60	V
		: KSB1116A	-80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	: KSB1116	-50	V
		: KSB1116A	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage		-6	V
lc	Collector Current (DC)		-1	Α
СР	* Collector Current (Pulse)		-2	Α
P <sub>C</sub>	Collector Power Dissipation		0.75	W
ТЈ	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		-55 ~ 150	°C

<sup>\*</sup> PW≤10ms, Duty Cycle≤50%

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -60V, I <sub>E</sub> =0			-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -6V, I_{C} = 0$			-100	nA
h <sub>FE1</sub>	* DC Current Gain : KSB1116	V <sub>CE</sub> = -2V, I <sub>C</sub> = -100mA	135		600	
	: KSB1116A		135		400	
h <sub>FE2</sub>		$V_{CE} = -2V, I_{C} = -1A$	81			
V <sub>BE</sub> (on)	* Base-Emitter On Voltage	V <sub>CE</sub> = -2V, I <sub>C</sub> = -50mA	-600	-650	-700	mV
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A, I <sub>B</sub> = -50mA		-0.2	-0.3	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	I <sub>C</sub> = -1A, I <sub>B</sub> = -50mA		-0.9	-1.2	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz		25		pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -2V, I <sub>C</sub> = -100mA	70	120		MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = -10V, I <sub>C</sub> = -100mA		0.07		μs
t <sub>STG</sub>	Storage Time	I <sub>B1</sub> = -I <sub>B2</sub> = -10mA		0.7		μs
t <sub>F</sub>	Fall Time	$V_{BE}$ (off)= 2~3V		0.07		μs

<sup>\*</sup> Pulse Test: PW ≤350μs, Duty Cycle≤2%

### **h**<sub>FE</sub> Classification

Classification	Y	G	L	
h <sub>FE1</sub>	135 ~ 270	200 ~ 400	300 ~ 600	

# **Typical Characteristics**

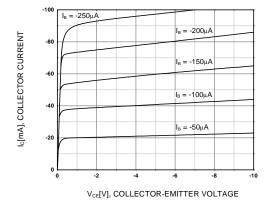


Figure 1. Static Characteristic

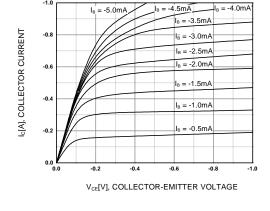


Figure 2. Static Characteristic

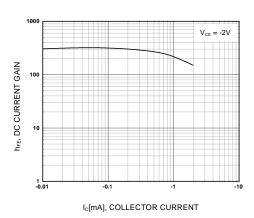


Figure 3. DC current Gain

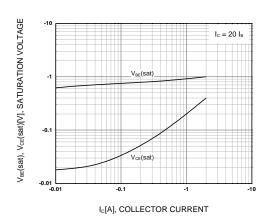


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

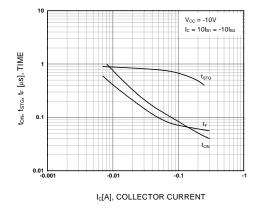


Figure 5. Switching Time

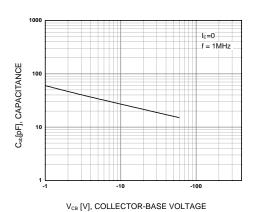


Figure 6. Collector Output Capacitance

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# Typical Characteristics (Continued)

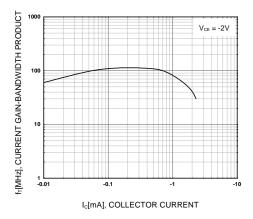


Figure 7. Current Gain Bandwidth Product

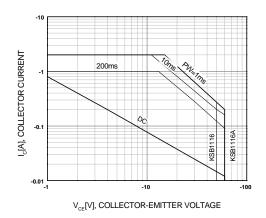


Figure 8. Safe Operating Area

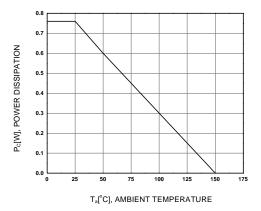


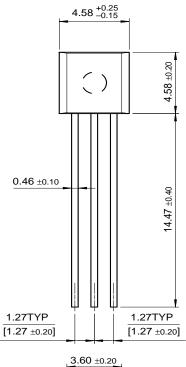
Figure 9. Power Derating

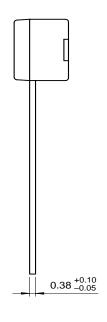
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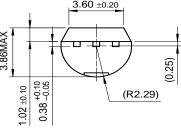
KSB1116/1116A

# **Package Demensions**

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